

DARE - radiation hardening by design

1.8 V Voltage Monitor
Product Brief

Product Overview

DARE22G VMON18 implements a 1.8 V voltage monitor for radiation-hardened applications in the commercial GF 22 nm FDSOI CMOS technology.

DARE22G exploits the intrinsic SEL immunity provided by the FDSOI technology in combination with special radiation-hardening-by-design (RHBD) techniques to mitigate TID and single-event effects.

Features

DARE22G VMON18 main functionalities include:

- Digital calibration with 15 trimming points
- Less than 50 μA static current consumption
- Typically 25 mV hysteresis
- TID immunity over 100 krad (SiO₂)
- SET immunity over 60 MeV.cm²/mg
- SEL immunity over 70 MeV.cm²/mg

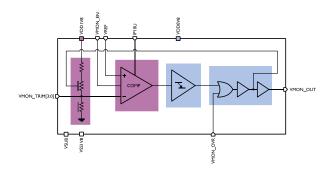
Block Diagram

The VMON18 macro consists of a digitally controlled resistive divider, a comparator, a level shifter, and digital buffers, all arranged in a feedback loop to generate hysteresis.

The integrated comparator requires an external high-precision $10~\mu A$ current source and a 0.6~V voltage reference to operate. These signals can be provided on chip by the DARE22G IVREF18 IP.

The voltage status output switches to I once the input reference voltage and all power supplies are stable.

Digital calibration is supported by input trimming bits controlling the internal resistive divider.



Pin Interface

Pin Name	Туре	Description	
VDD1V8	Power	I/O power supply	
VDD0V8	Power	Core power supply	
VSS1V8	Ground	Ground supply	
VSUB	Ground	P-substrate bias voltage	
VREF	Analog	0.6 V reference voltage	
IP10U	Analog	10 μA bias current	
VMON_OUT	Digital	Output status	
VMON_EN	Digital	Enable	
VMON_OVR	Digital	Output override	
VMON_TRIM[3:0]	Digital	Trimming bits	

Physical Dimensions

DARE22G VMON18 is implemented as a core macro.

IP Name	Width	Height
VMON18	125 µm	40 µm

Contact

For further information, please contact us at dare@imec.be

Operating Conditions

Performance and reliability are not guaranteed outside these recommended operating boundaries.

Parameter	Name	Minimum	Typical	Maximum	Unit
Core supply voltage	V_{DD0V8}	0.72	0.8	0.88	٧
I/O supply voltage	V_{DDIV8}	1.62	1.8	1.98	V
Operating temperature	Tı	-40	25	125	°C
TID immunity	TID	100			krad (SiO ₂)
SET hardening	SET_{th}	60			MeV.cm ² /mg
SEL hardening	SEL_th	70			MeV.cm ² /mg